

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ECH8675 — General-Purpose Switching Device Applications

Features

- · 1.8V drive
- · Composite type, facilitating high-density mounting
- · Halogen free compliance
- · Protection diode in

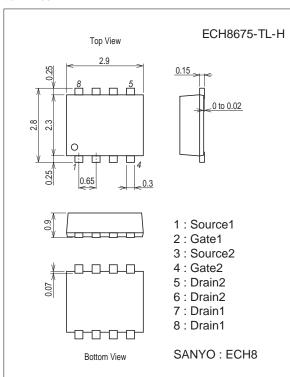
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-4.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-30	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm) 1unit	1.3	W
Total Power Dissipation	PT	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	C
Storage Temperature	Tstg		-55 to +150	C

Package Dimensions

unit : mm (typ) 7011A-001



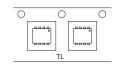
Product & Package Information

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

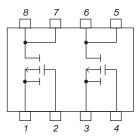
Packing Type: TL



Marking



Electrical Connection

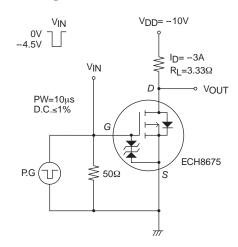


ECH8675

Electrical Characteristics at Ta=25°C

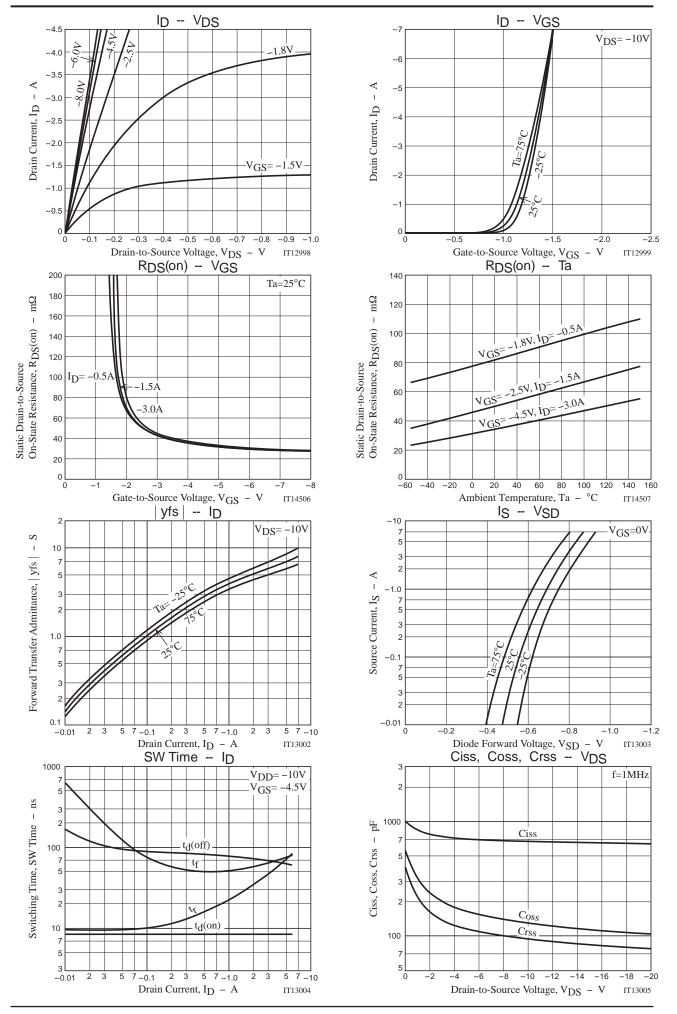
Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Syllibol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-20V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-0.4		-1.3	V	
Forward Transfer Admittance	yfs	V _D S=-10V, I _D =-3A	3.5	5.9		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-3A, V _G S=-4.5V		35	46	mΩ	
	R _{DS} (on)2	I _D =-1.5A, V _G S=-2.5V		51	72	mΩ	
	R _{DS} (on)3	I _D =-0.5A, V _G S=-1.8V		75	115	mΩ	
Input Capacitance	Ciss			670		pF	
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		130		pF	
Reverse Transfer Capacitance	Crss			94		pF	
Turn-ON Delay Time	t _d (on)			8.4		ns	
Rise Time	t _r	One are a liftered Treet Circuit		45		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		69		ns	
Fall Time	tf			63		ns	
Total Gate Charge	Qg			7.3		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-4.5A		1.3		nC	
Gate-to-Drain "Miller" Charge	Qgd			2.1		nC	
Diode Forward Voltage	V _{SD}	I _S =-4.5A, V _{GS} =0V		-0.82	-1.2	V	

Switching Time Test Circuit



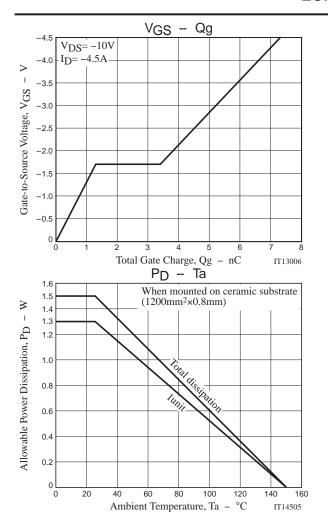
Ordering Information

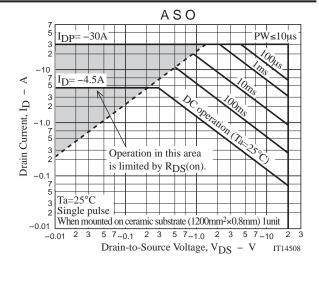
Device	Package	Shipping	memo	
ECH8675-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free	



ECH8675

IT14505



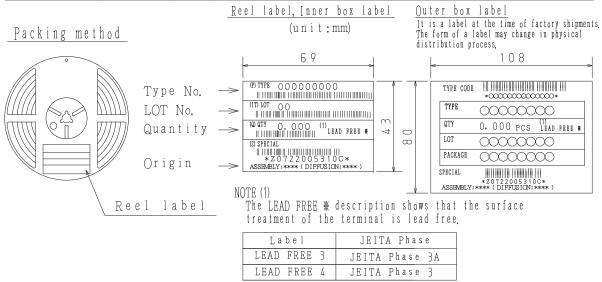


Embossed Taping Specification

ECH8675-TL-H

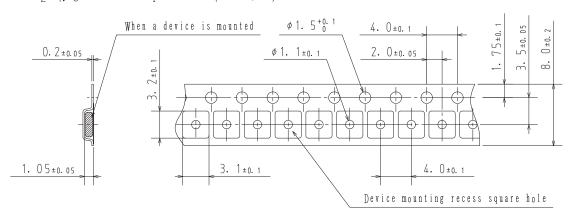
1. Packing Format

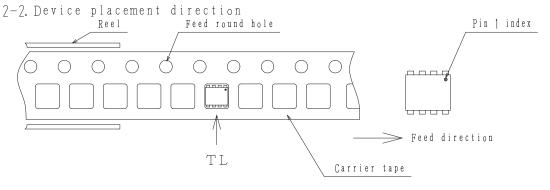
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained
					Dimensions:mm (external)	Dimensions:mm (external)
					183×72×185	440×195×210



2. Taping configuration

2-1. Carrier tape size (unit:mm)





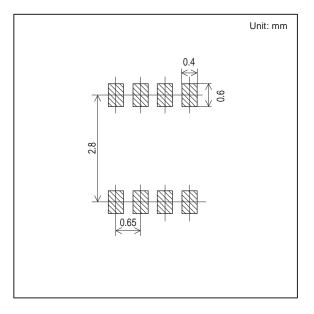
Those with pin 1 index on the feed hole side · · · · · TL

Outline Drawing

ECH8675-TL-H

Mass (g) Unit 0.02 For reference mm 2. 924.06 8 7 6 5 LOT No. PINET 2. 924.05 2. 924.05 8 7 6 5 1. 0. 15/14, 15 1. 0. 0.02

Land Pattern Example



Note on usage: Since the ECH8675 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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